

Docket No.: 061352-0051



*C of C*  
**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of	:	Customer Number: 20277
Yoshiaki HASEGAWA, et al.	:	Confirmation Number: 4412
Application No.: 10/687,647	:	Group Art Unit: 2822
Patent No.: 6,884,648 B2	:	
Filed: October 20, 2003	:	Examiner: PICARDAT, Kevin M.
Issued: April 26, 2005	:	
For: METHOD FOR FABRICATING SEMICONDUCTOR LIGHT EMITTING DEVICE	:	

**REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 CFR 1.322**

Mail Stop Box 4 / Certificates of Correction  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In reviewing the above-identified patent, a printing error was discovered therein requiring correction in order to conform the Official Record in the application.

The error noted is set forth on the attached copy of form PTO-1050 Rev. 2-93 in the manner required by the Commissioner's Notice.

Specifically, on pages 1 and 2 of the title page, under "OTHER PUBLICATIONS", there are five spelling errors as shown on the attached 1050 form. A copy of Applicant's 1449 form, considered by the Examiner on 12/08/04, showing the correct versions, is attached for your information and convenience.

**Certificate  
'AUG 1 2 2005  
of Correction**

**AUG 1 5 2005**

**10/687,647**

Patent No. 6,884,648 B2

The change requested herein occurred as a result of printing the Letters Patent and the Certificate should be issued without expense under Rule 322 of the Rules of Practice. Accordingly, Applicants request issuance of the Certificate of Correction.

Please charge any shortage in fees due in connection with the filing of this paper to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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**Date: August 10, 2005**

**Please recognize our Customer No. 20277  
as our correspondence address.**

WDC99 1119501-1.061352.0051

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 6,884,648 B2

DATED : April 26, 2005

INVENTOR(S) : Yoshiaki HASEGAWA, et al.

It is certified that error appears in the above-identified patent and that said Letter Patent is hereby corrected as shown below:

**TITLE PAGE**

Under "OTHER PUBLICATIONS",

line 1, change the phrase ""InGaN Multiquantum-" to -- "InGaN Multiquantum --;

line 3, change "Strained-Layer Superlattices" to -- Strained-Layer Superlattices --;

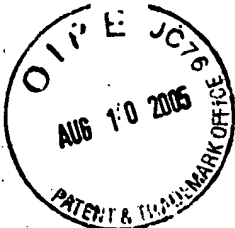
**Page 2 of the TITLE PAGE**

Under "OTHER PUBLICATIONS",

line 1, change "Lateral Expilaxial" to -- Lateral Epitaxial --;  
right hand column, in the Shuji Nakamura, et al article,

line 1, change ""InGaN/GaNAL/GaN" to --InGaN/GaN/AlGaN --;

lines 2-3, change "Superlatices" to -- Superlattices --.



SHEET 1 OF 1

INFORMATION DISCLOSURE  
CITATION IN AN  
APPLICATIONATTY. DOCKET NO.  
61352-051SERIAL NO.  
10/687,647APPLICANT  
Yoshiaki HASEGAWA, et al.FILING DATE  
October 20, 2003GROUP  
2811

(PTO-1449)

## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
W		US 5,757,833	05/26/1998	Arakawa et al.	Corresponds to JP 9-191150
		US			
		US			
		US			

## FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number - Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
W		JP P2001-244560A	09/07/2001	SONY CORP		(Japan w/English Abstract)	
		JP P2000-196188A	07/14/2000	TOSHIBA CORP		(Japan w/English Abstract)	
		JP 9-191150	07/22/1997		Corresponds to US 5,757,833		
		JP 63-1370	01/07/1988	SANYO ELECTRIC CO., LTD.		(Front page of Japanese Patent and English Abstract)	
		JP 63-34992	02/15/1988	NEC CORP		(Japan w/English Abstract)	
		JP 5-343813	12/24/1993	ASAHI GLASS CO LTD		(Japan w/English Abstract)	
W		JP 5-259079	10/08/1993	NEC CORP		(Japan w/English Abstract)	

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
W		Shuji NAKAMURA, "InGaN Multiquantum-Well-Structure Laser Diodes with GaN-AlGaIn Modulation-Doped Strained-Layer Superlattices", IEEE Journal of Selected Topics in Quantum Electronics, Vol. 4, No. 3, May/June 1998, p. 483-489
		H. MARCHAND, et al., "Mechanisms of Lateral Epitaxial Overgrowth of Gallium Nitride by Metalorganic Chemical Vapor Deposition", Journal of Crystal Growth, 185 (1998) 328-332
		Michael KNEISSL, et al., "Performance and Degradation of Continuous-wave InGaN Multiple-Quantum-Well Laser Diodes on Epitaxially Laterally Overgrown GaN Substrates", Applied Physics Letters, Vol. 77, No. 13, September 25, 2000, pages 1931-1933
		Shuji NAKAMURA, "UV/Blue/Green InGaN-Based LEDs and Laser Diodes Grown on Epitaxially Laterally Overgrown GaN", IEICE Trans. Electron., Vol. E83-C, No. 4, April 2000, p. 529-535
W		Shuji NAKAMURA, et al., "InGaN/GaN/AlGaIn-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices Grown on an Epitaxially Laterally Overgrown GaN Substrate", Applied Physics Letters, Vol. 72, No. 2, pages 211-213 (1998)

EXAMINER

DATE CONSIDERED

K. P. L. L. L.

M. J. L. L.

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

AUG 15 2005